

Schottky Diodes: MNM 200 Series

Medium Barrier Schottky Mixer Diodes

Description

The **MicroMetrics** MNM 200 series of Medium Barrier Schottky diodes are metal semiconductor junction devices that have a typical short reverse recovery time. This allows their use at high microwave frequencies when the performance of the n-type may be reduced. The forward I-V of schottky diodes is determined by the junction metal used. For every different metal selection there is a different forward voltage characteristic or "Barrier Height". These devices are best suited for applications through 26 GHz.

Applications

Medium Barrier Schottky Mixer diodes are ideally suited for use in mixers, doublers and modulators.

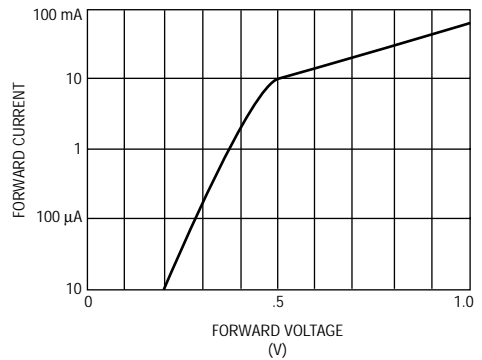
Features

- Multi-Junction Chips
- Low 1/F Noise
- Small Junction Capacitance

Packaging

- Chip, Glass, Ceramic, Beam Lead

Typical Performance



Electrical Characteristics

Breakdown Voltage @10 μ A MIN (V)	Forward Voltage @1 mA MAX (V)	Junction Capacitance @0 Vdc 1 MHz TYP (pF)	Series Resistance @5 mA TYP (Ohms)	Tangential Signal Sensitivity TYP (dB)	Part Number
3.0	0.35	0.08	15.0	-52	MNM200
3.0	0.35	0.1	15.0	-50	MNM201
3.0	0.35	0.12	12.0	-48	MNM202
3.0	0.35	0.14	8.0	-45	MNM203
4.0	0.375	0.08	15.0	-52	MNM204
4.0	0.375	0.1	15.0	-50	MNM205
4.0	0.375	0.12	12.0	-48	MNM206
4.0	0.375	0.14	8.0	-45	MNM207
5.0	0.4	0.08	15.0	-52	MNM208
5.0	0.4	0.1	15.0	-50	MNM209
5.0	0.4	0.12	12.0	-48	MNM210
5.0	0.4	0.14	8.0	-45	MNM211
6.0	0.45	0.08	15.0	-52	MNM212
6.0	0.45	0.1	15.0	-50	MNM213
6.0	0.45	0.12	12.0	-48	MNM214
6.0	0.45	0.14	8.0	-45	MNM215

Maximum Ratings

Operating Temperature	-55°C to + 150°C
Storage Temperature	-65°C to + 200°C
Power Dissipation @25°C	250mW (derate linearly to zero at 150°C)

